

**• General Description**

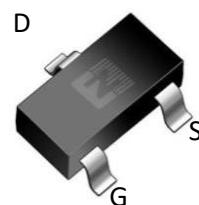
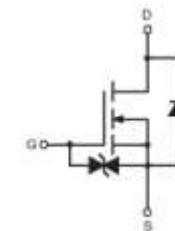
N-CHANNEL MOSFET in a SOT-23 Plastic Package.

• Features

- Sensitive gate trigger current and Low Holding current.
- ESD protected up to 1KV.
- Very fast switching

• Application

- switching and phase control applications.
- SMPS 2nd Synchronous Rectifier

• Product Summary $V_{DS} = 60V$ $R_{DS(ON)} = 5\Omega$ $I_D = 300mA$ 

SOT-23

• Ordering Information:

Part NO.	ZM2N7002K
Marking	ZM2N7002
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

• Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Drain-Gate Voltage	V_{DGR}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D @ T_C = 25^\circ C$	300	mA
	$I_D @ T_C = 75^\circ C$	228	mA
	$I_D @ T_C = 100^\circ C$	189	mA
Pulsed Drain Current	I_{DM}	800	mA
Total Power Dissipation	P_D	350	mW
Storage Temperature	T_{STG}	-55 to 150	°C

•Electronic Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$\text{V}_{\text{GS}} = 0\text{V}, \text{I}_D = 10\text{uA}$	60			V
Gate Threshold Voltage	$\text{V}_{\text{GS}(\text{TH})}$	$\text{V}_{\text{GS}} = \text{V}_{\text{DS}}, \text{I}_D = 1\text{mA}$	1.0	1.6	2.5	V
Drain-Source Leakage Current	I_{DSS}	$\text{V}_{\text{DS}} = 60\text{V}, \text{V}_{\text{GS}} = 0\text{V}$			1.0	uA
Gate- Source Leakage Current	I_{GSS}	$\text{V}_{\text{GS}} = \pm 20\text{V}, \text{V}_{\text{DS}} = 0\text{V}$			± 10	uA
Static Drain-source On Resistance	$\text{R}_{\text{DS}(\text{ON})}$	$\text{V}_{\text{GS}} = 10\text{V}, \text{I}_D = 0.5\text{A}$			5	Ω
		$\text{V}_{\text{GS}} = 5\text{V}, \text{I}_D = 0.05\text{A}$			5.5	Ω
Drain-Source On-Voltage	$\text{V}_{\text{DS}(\text{ON})}$	$\text{V}_{\text{GS}} = 10\text{V}, \text{I}_D = 500\text{mA}$			2.5	V
Drain-Source On-Voltage	$\text{V}_{\text{DS}(\text{ON})}$	$\text{V}_{\text{GS}} = 5.0\text{V}, \text{I}_D = 50\text{mA}$			0.275	V
Forward Transfer Admittance	Y_{fs}	$\text{V}_{\text{DS}} = 5\text{V}, \text{I}_D = 0.2\text{A}$	80			mS
Source-Drain Voltage	V_{SD}	$\text{I}_S = 500\text{mA}$			1.28	V

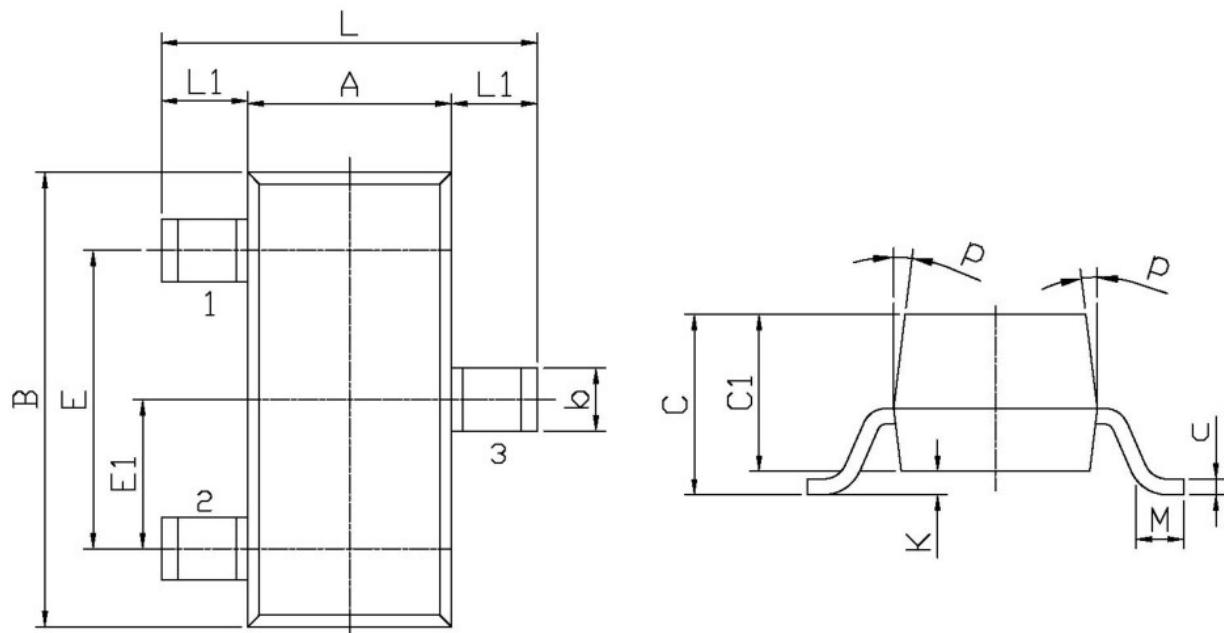
•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$\text{V}_{\text{GS}} = 0\text{V}$ $\text{V}_{\text{DS}} = 25\text{V}$ $f = 1\text{MHz}$	-		50	pF
Output capacitance	C_{oss}		-		25	
Reverse transfer capacitance	C_{rss}		-		5	
Turn – on delay time	$\text{t}_{\text{d}(\text{on})}$	$\text{V}_{\text{DD}} = 25\text{V} \text{ I}_D = 500\text{mA}$			20	ns
Turn - off delay time	$\text{t}_{\text{d}(\text{off})}$	$\text{R}_G = 25\Omega \text{ R}_L = 25\Omega$ $\text{V}_{\text{gen}} = 10\text{V}$			40	ns



•Dimensions(SOT23-3)

Unit: mm



Unit: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
L	2.2	2.7	C	1.30Max	
L1	0.45	0.65	C1	0.90	1.20
A	1.15	1.50	c	0.05	0.20
B	2.70	3.10	K	0	0.10
E	1.70	2.10	M	0.20MIN	
E1	0.85	1.05	P	7°	
b	0.35	0.55			

**•Electrical Characteristic Curve**